

# PSMN5R0-80BS

# N-channel 80 V, 5.1 m $\Omega$ standard level MOSFET in D2PAK Rev. 1 — 20 March 2012

**Product data sheet** 

#### 1. **Product profile**

### 1.1 General description

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see Figure 1	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	270	W
Tj	junction temperature			-55	-	175	°C
Static char	acteristics						
R <sub>DSon</sub> drain-source on-state resista	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 °C;$ see <u>Figure 13</u> ; see <u>Figure 12</u>		-	7.19	8.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12		-	4.36	5.1	mΩ
Dynamic c	haracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 40 \text{ V};$		-	21	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	101	-	nC
Avalanche	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 100 A; $V_{sup}$ ≤ 80 V; $R_{GS}$ = 50 Ω; unclamped		-	-	396	mJ

<sup>[1]</sup> Continuous current is limited by package



# 2. Pinning information

Table 2. Pinning information

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make connection to pin 2

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R0-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN5R0-80BS	PSMN5R0-80BS

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		, ,				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	80	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	80	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	[1]	-	100	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	[1]	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3		-	598	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	270	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	ain diode					
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	598	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le 80$ V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	396	mJ

### [1] Continuous current is limited by package

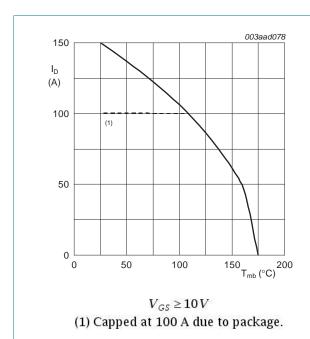
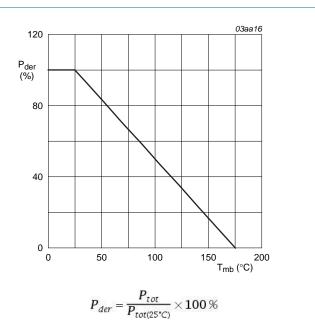


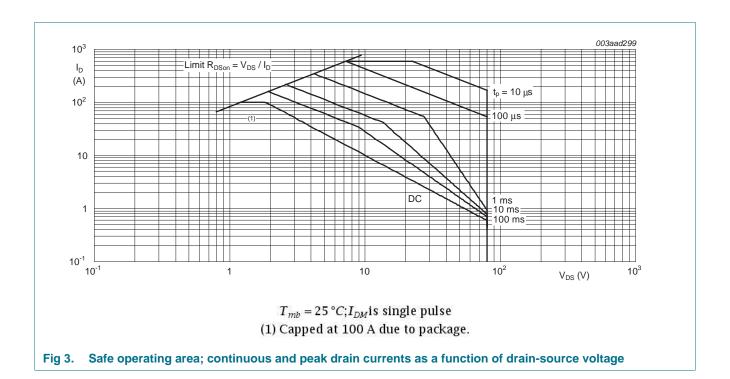
Fig 1. Continuous drain current as a function of mounting base temperature



ig 2. Normalized total power dissipation as a function of mounting base temperature

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### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.3	0.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

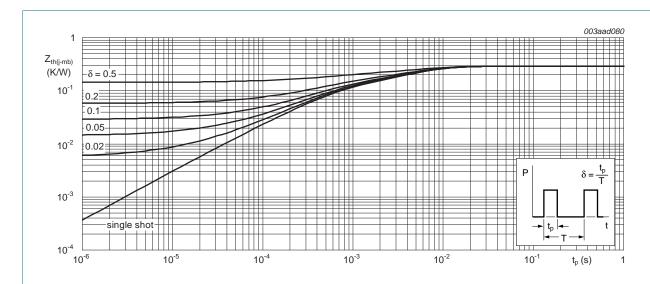


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

## 7. Characteristics

**Table 7. Characteristics** 

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 10	-	-	4.6	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see Figure 11; see Figure 10	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	8	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	150	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	10.46	12.3	Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see Figure 13; see Figure 12	-	7.19	8.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	4.36	5.1	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.95	-	Ω
Dynamic c	haracteristics					
Q <sub>G(tot)</sub> total gate charge		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	87	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	101	-	nC
$Q_GS$	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	26	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	18	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	8	-	nC
$Q_{GD}$	gate-drain charge		-	21	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}$ ; $V_{DS} = 40 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.2	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	6793	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	913	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	350	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 10 \text{ V};$	-	33	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	21	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	73	-	ns
t <sub>f</sub>	fall time		-	14	-	ns

116

nC

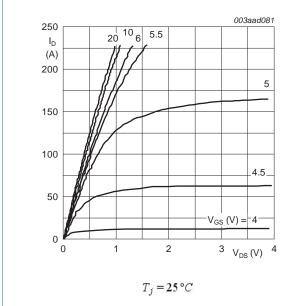
 $Q_{r}$ 

### N-channel 80 V, 5.1 m $\Omega$ standard level MOSFET in D2PAK

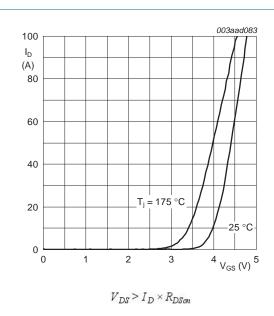
Characteristics ... continued Table 7. Tested to JEDEC standards where applicable.

recovered charge

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	8.0	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = 100 \text{ A/}\mu\text{s}$ ;	-	56	-	ns
0	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$	_	116	_	nC



Output characteristics: drain current as a Fig 5. function of drain-source voltage; typical values



Transfer characteristics: drain current as a Fig 6. function of gate-source voltage; typical values

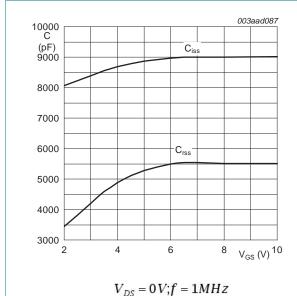
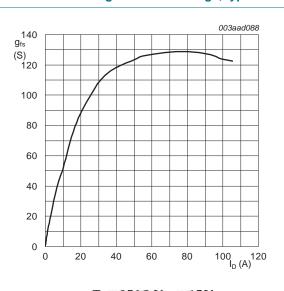


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25 \,{}^{\circ}C; V_{DS} = 15 \, V$ 

Fig 8. Forward transconductance as a function of drain current; typical values

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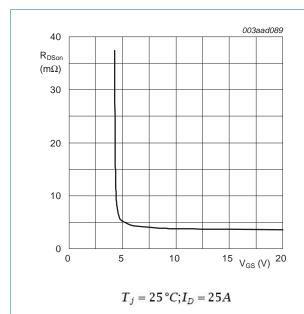


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

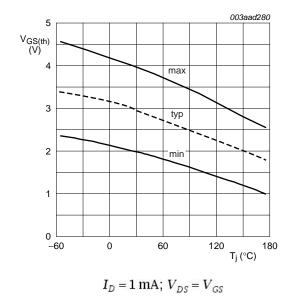


Fig 10. Gate-source threshold voltage as a function of junction temperature

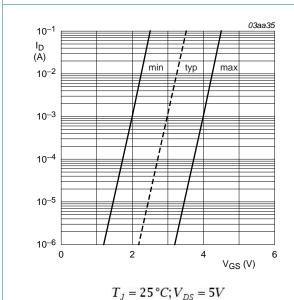


Fig 11. Sub-threshold drain current as a function of gate-source voltage

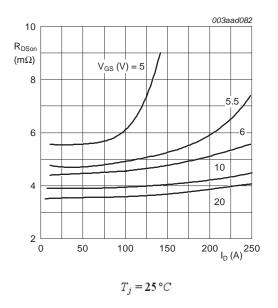


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

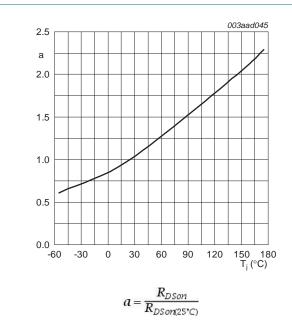


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

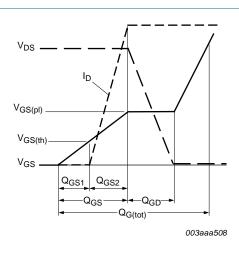
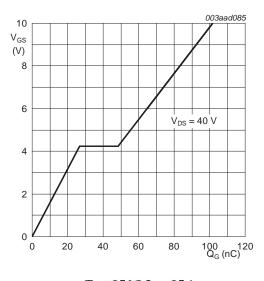
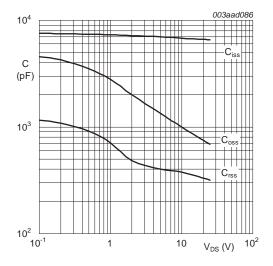


Fig 14. Gate charge waveform definitions



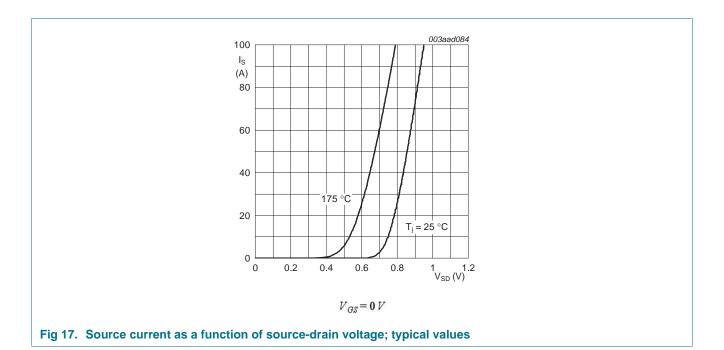
 $T_j = 25\,^{\circ}C; I_D = 25A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



## 8. Package outline

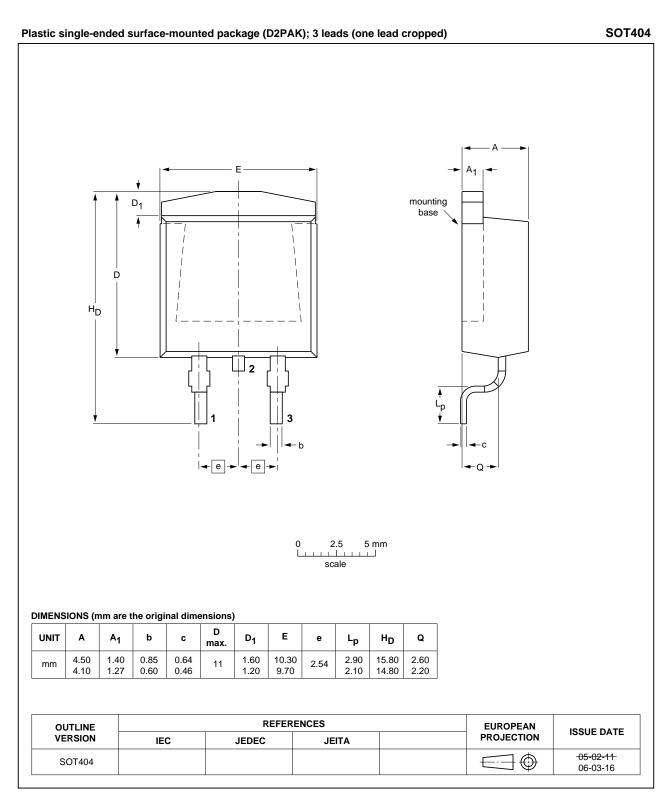


Fig 18. Package outline SOT404 (D2PAK)

# 9. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN5R0-80BS v.1	20120320	Product data sheet	-	-

### 10. Legal information

#### 10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# PSMN5R0-80BS

### N-channel 80 V, 5.1 m $\Omega$ standard level MOSFET in D2PAK

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